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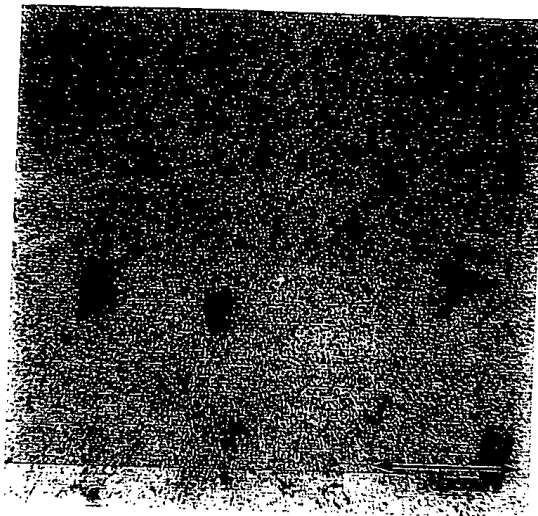


Fig. 1A

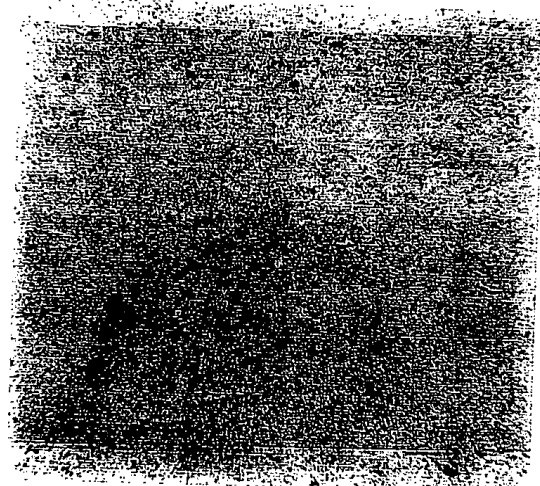


Fig. 1B

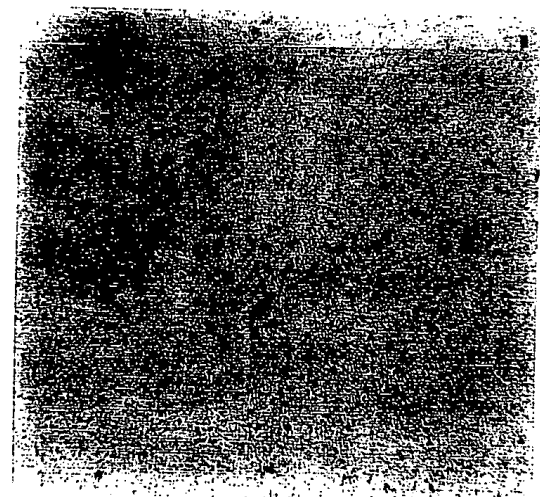


Fig. 1C

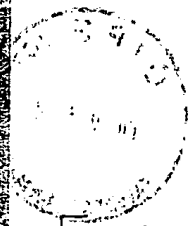


Fig. 2A



Fig. 2B

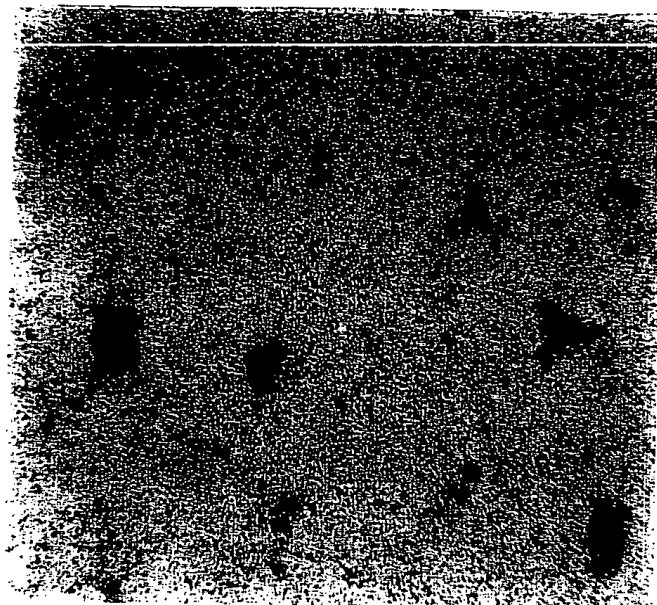


Fig. 3A



Fig. 3B

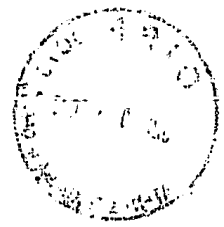
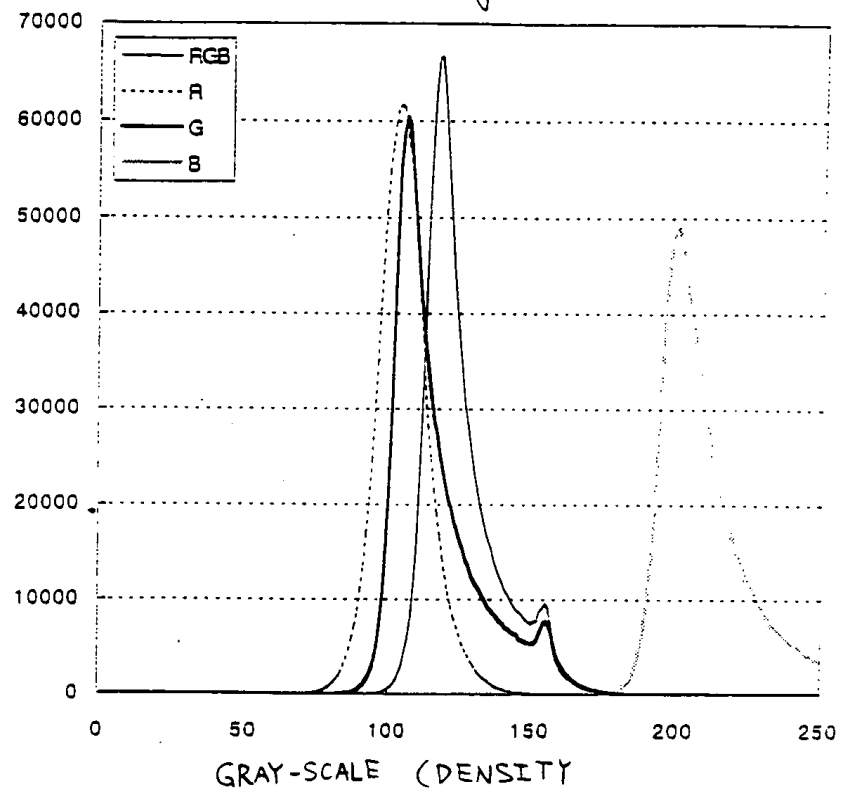


Fig. 4



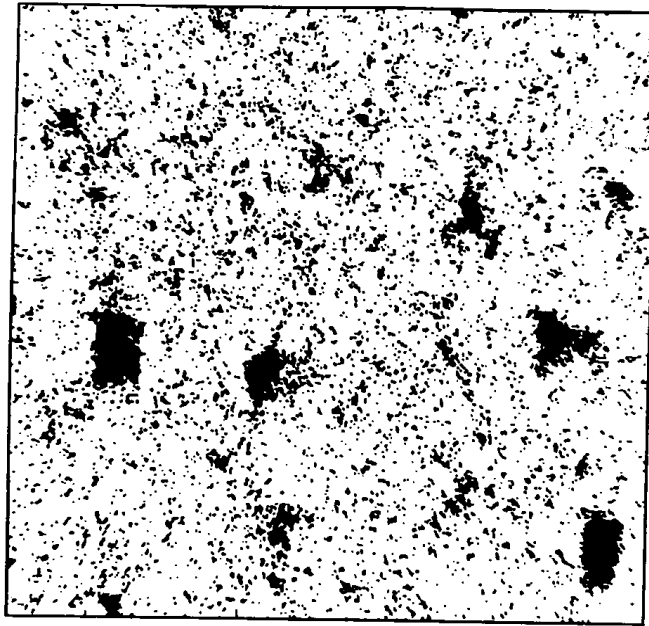


Fig. 5A

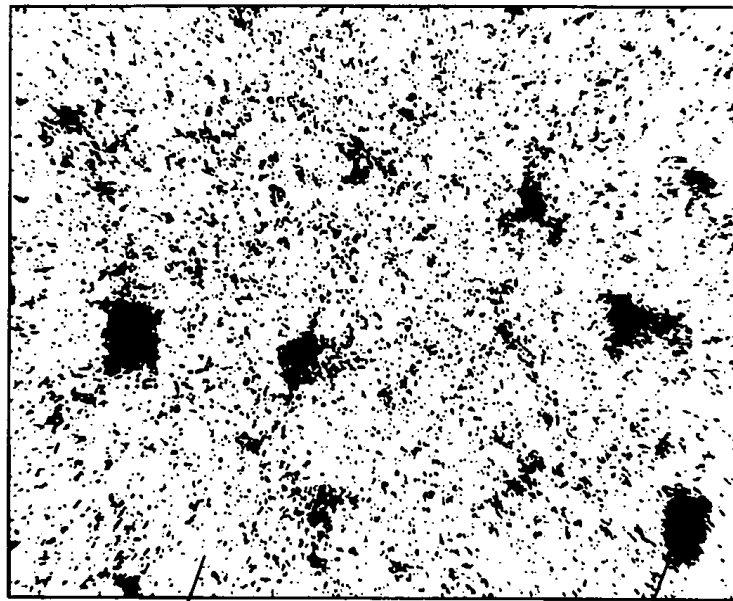
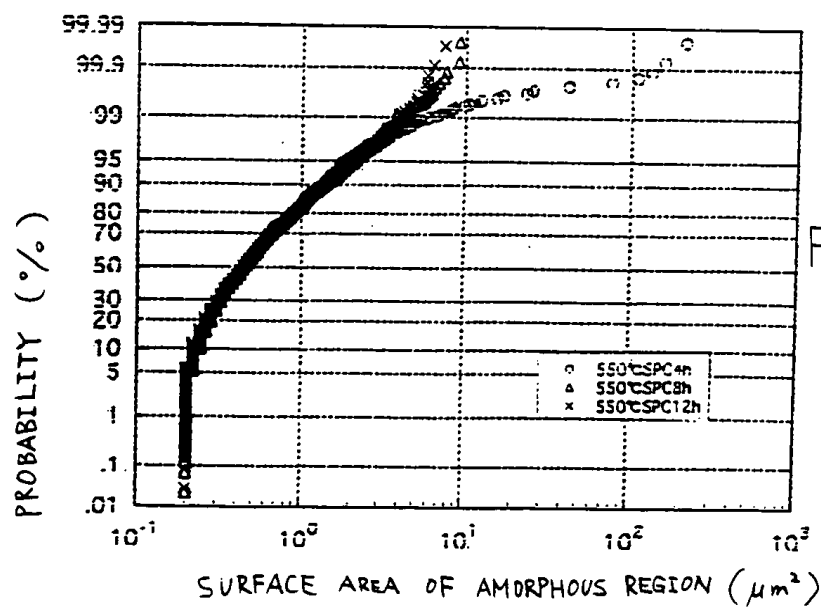
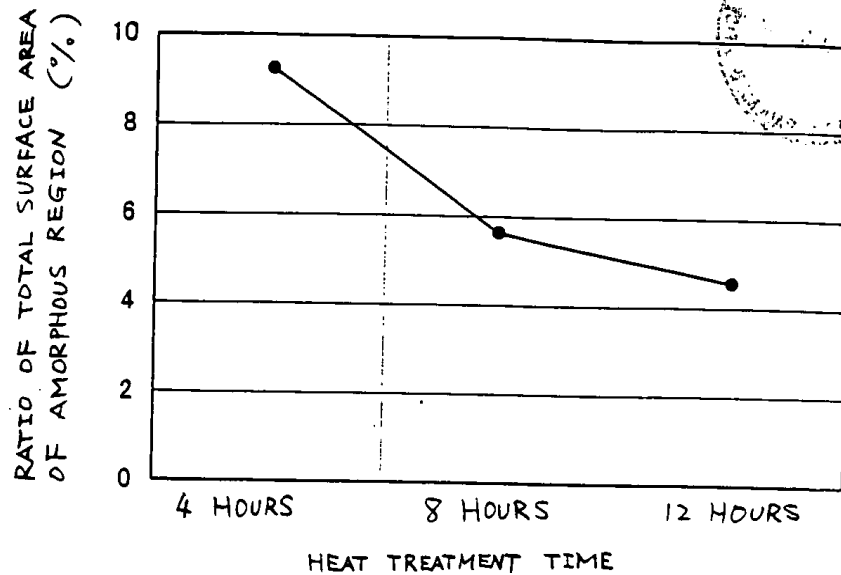


Fig. 5B

5001

5002



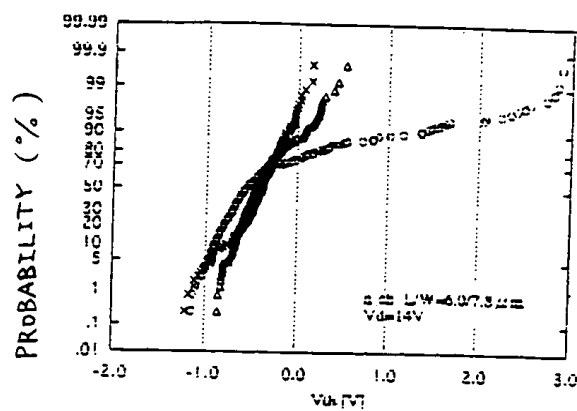


Fig. 7A

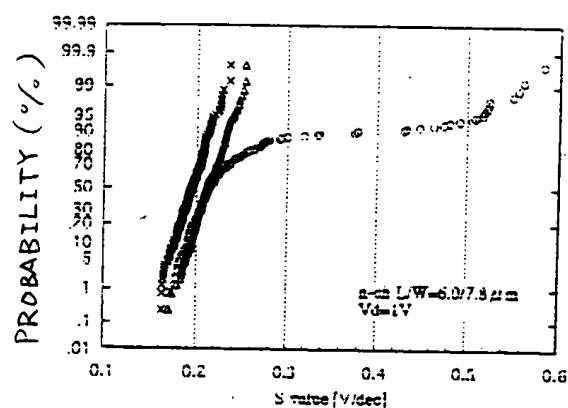


Fig. 7B

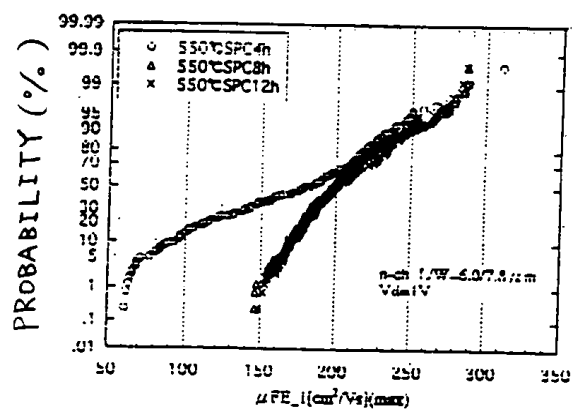


Fig. 7C

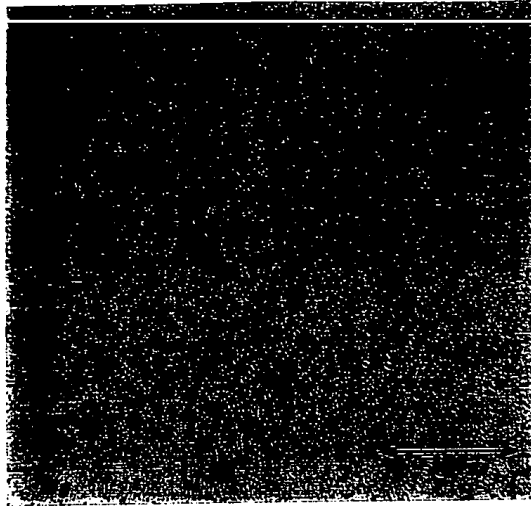


Fig. 8A

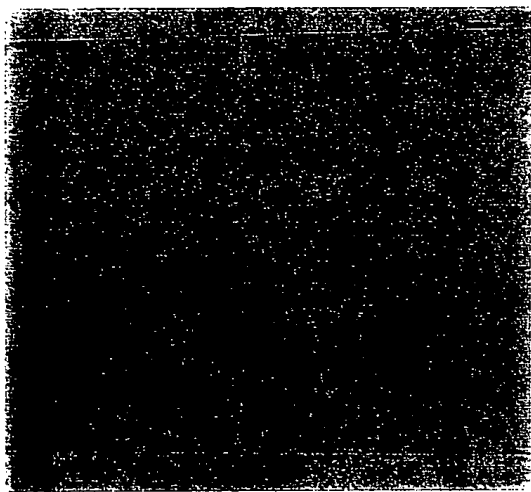


Fig. 8B

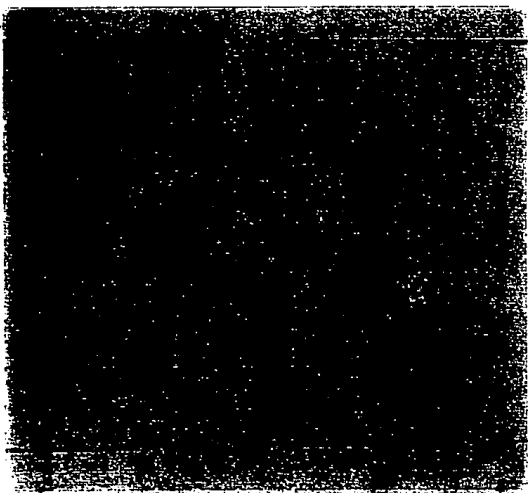


Fig. 8C

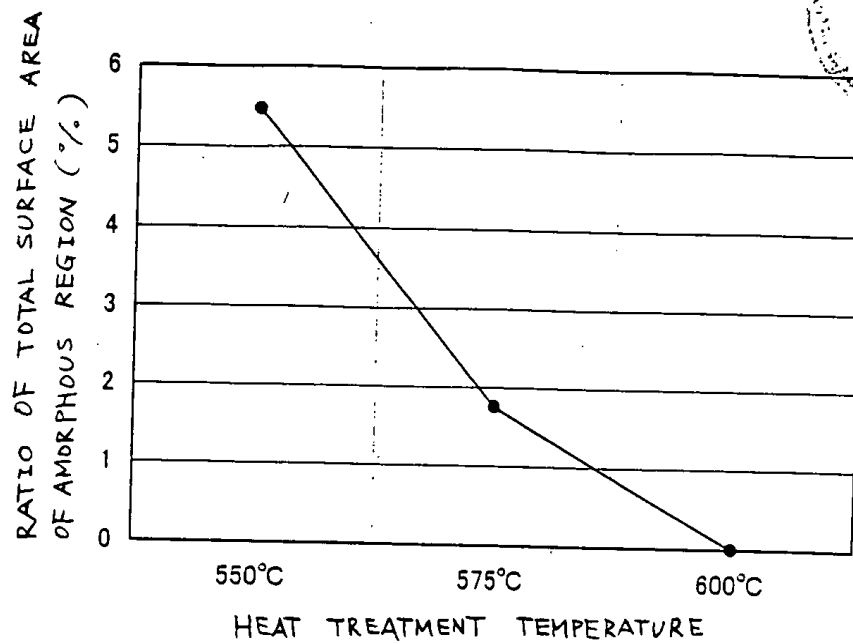


Fig. 9A

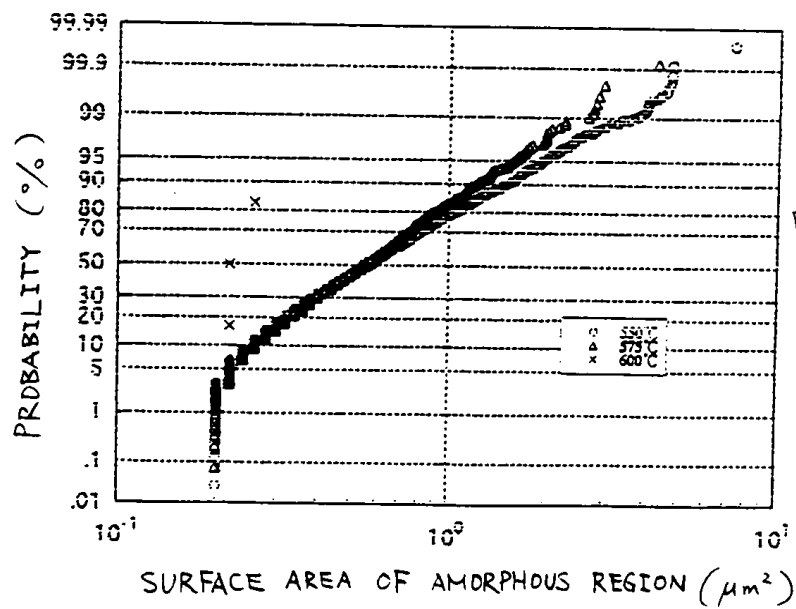


Fig. 9B

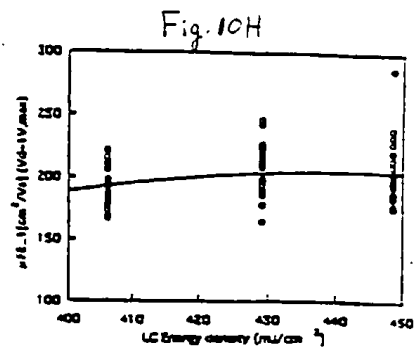
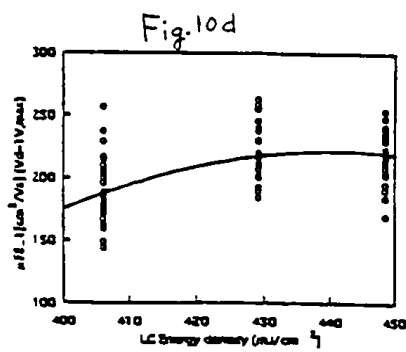
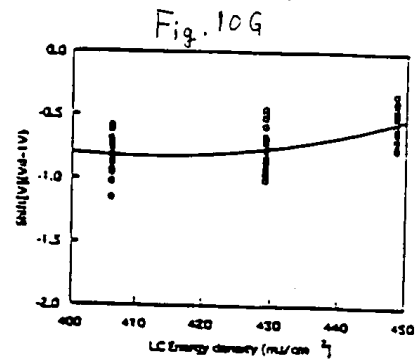
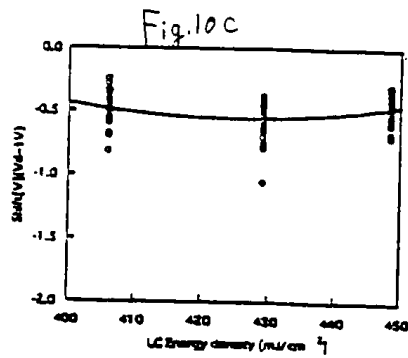
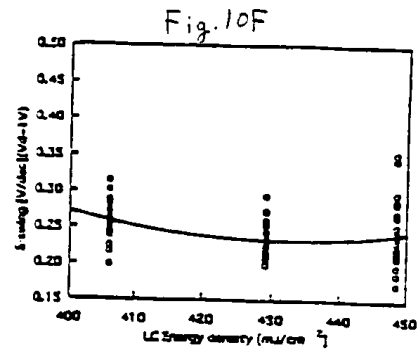
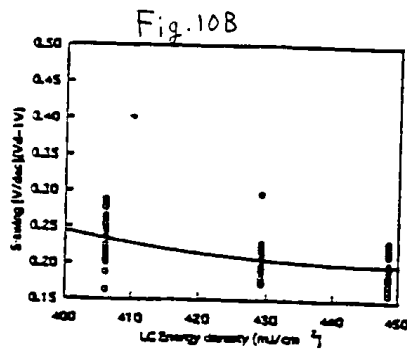
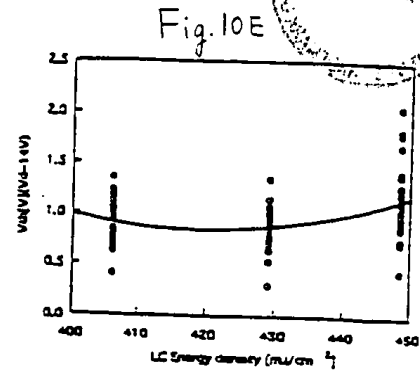
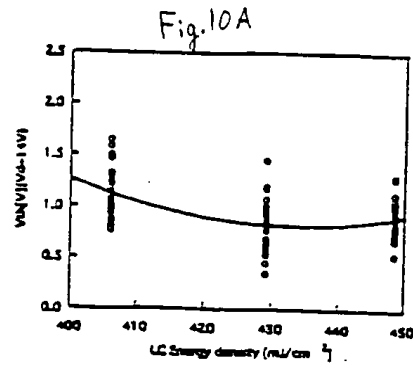


Fig. 11A

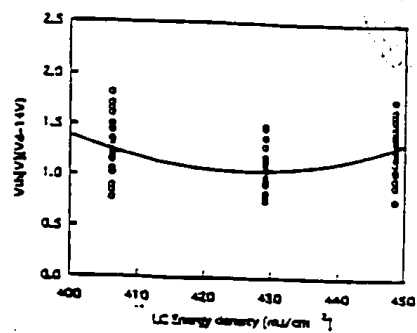


Fig. 11B

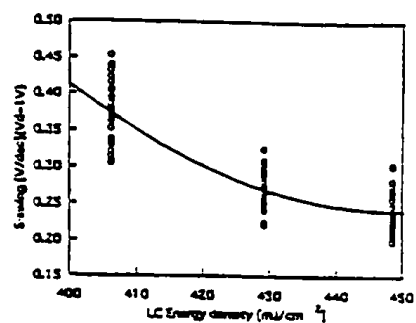


Fig. 11c

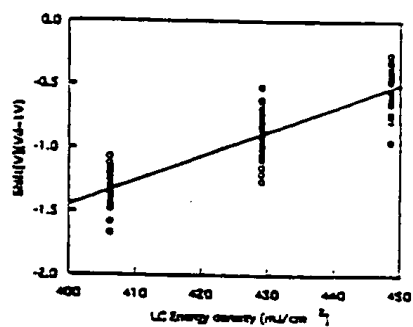
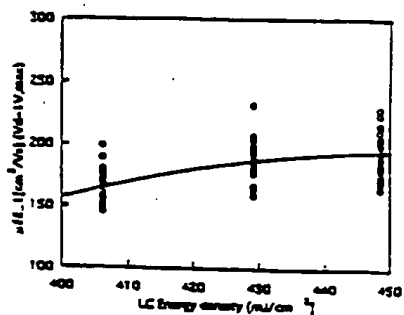
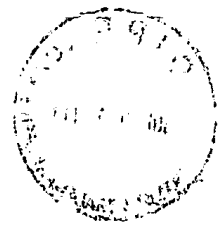
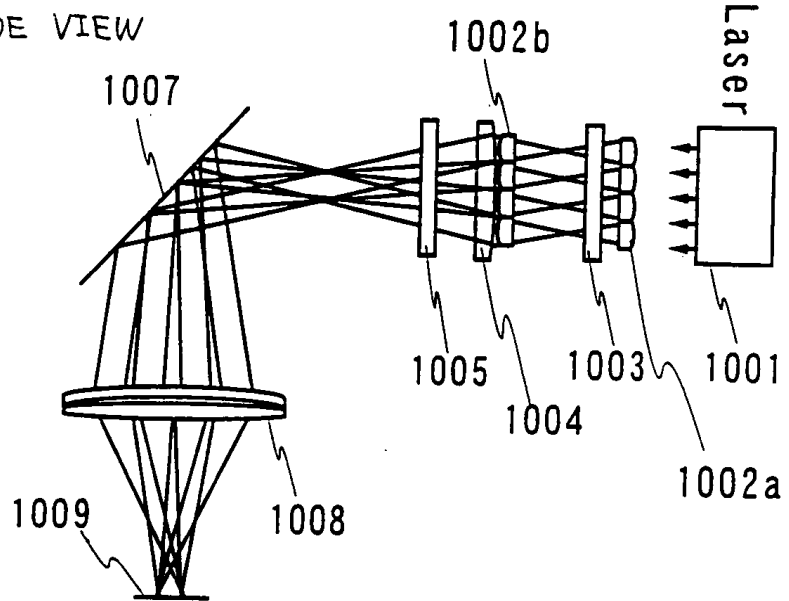


Fig. 11d





SIDE VIEW



TOP VIEW

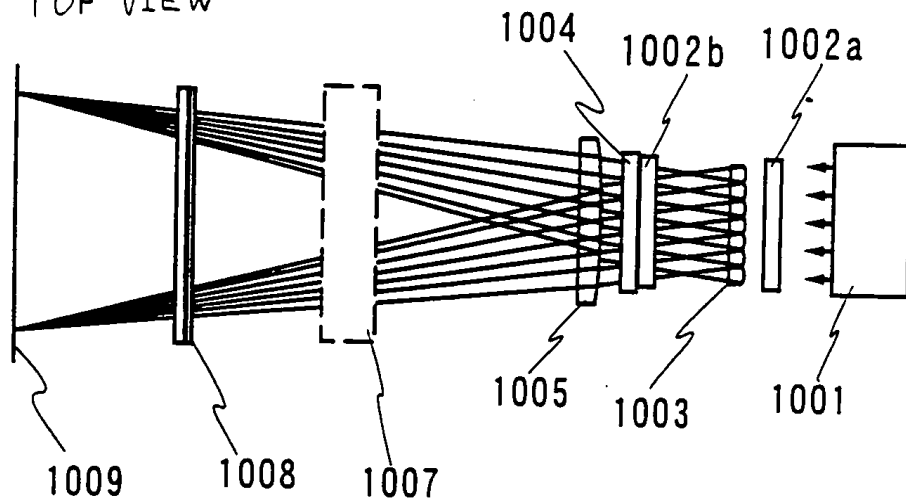
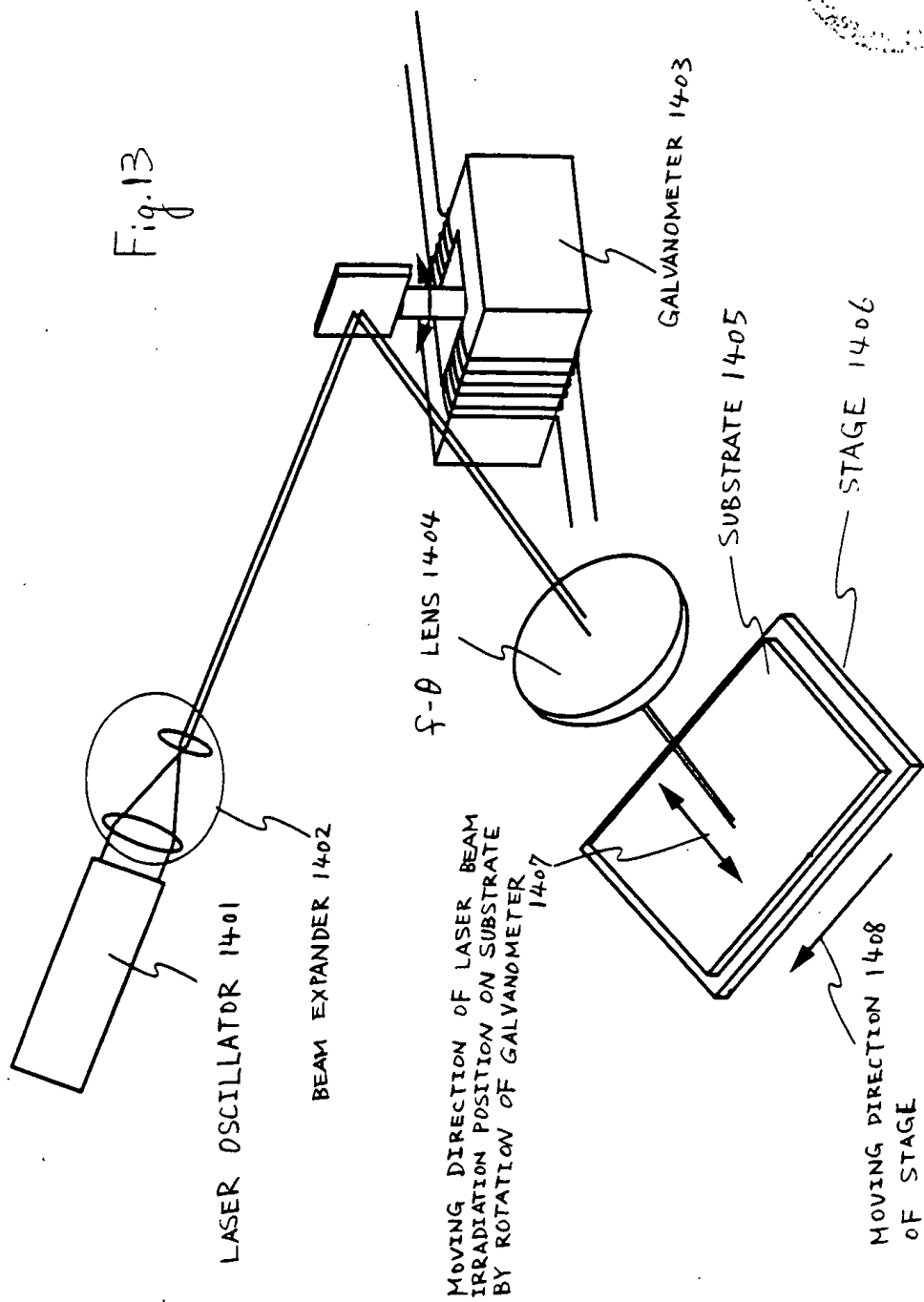
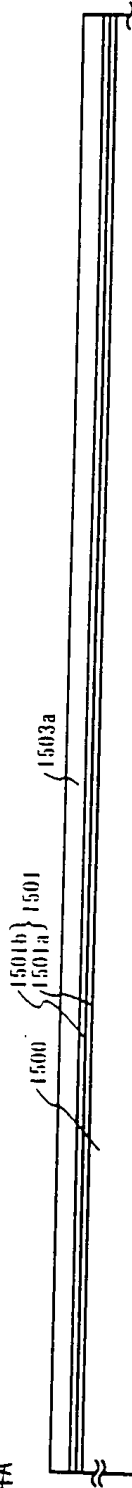


Fig. 12



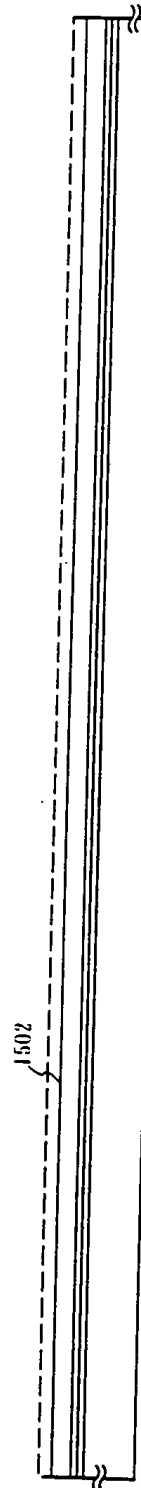
STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

Fig. 14A



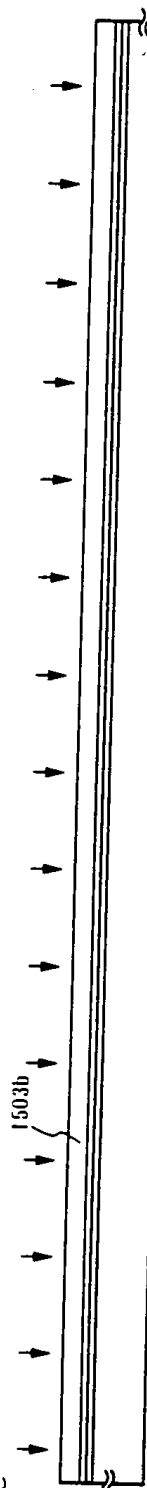
FORMATION OF METAL CONTAINING LAYER / HEAT TREATMENT

Fig. 14B



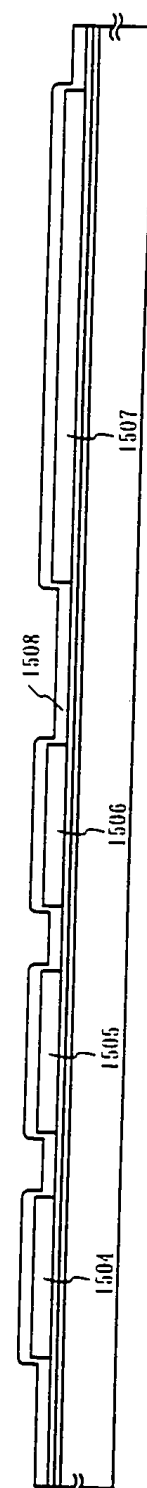
LASER BEAM IRRADIATION

Fig. 14C



STEP OF FORMING MASK LAYER

Fig. 14D



CHANNEL DOPING STEP

Fig. 14E

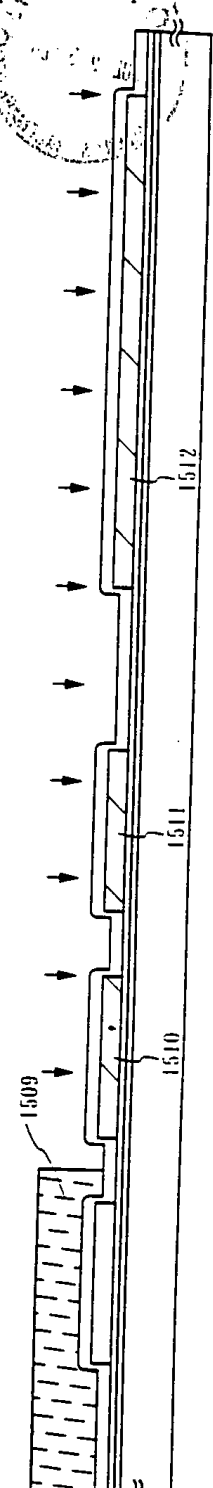


Fig. 15A n^- DOPE STEP

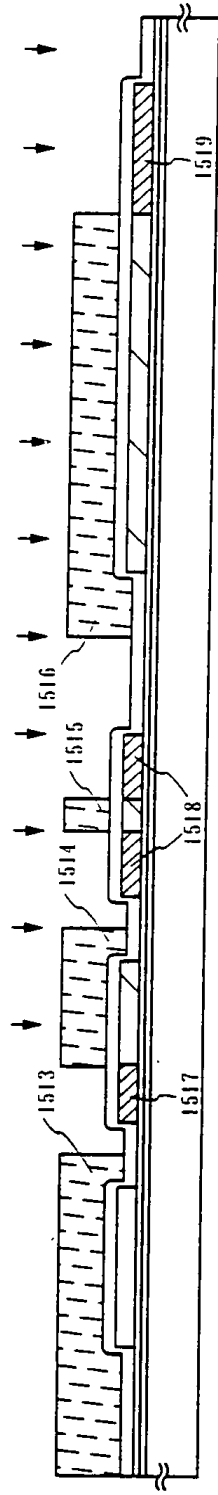


Fig. 15B STEP OF REMOVING MASK LAYER/LASER ACTIVATION STEP/STEP OF FORMING GATE INSULATING FILM

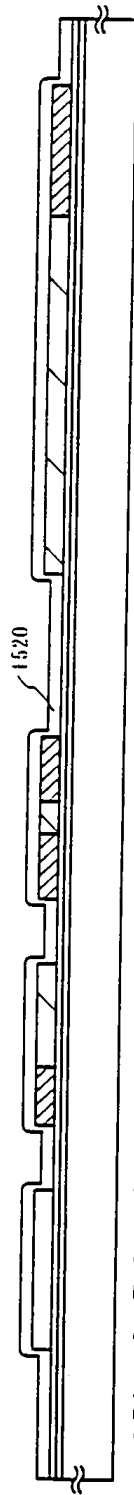


Fig. 15C STEP OF FORMING FIRST CONDUCTIVE LAYER

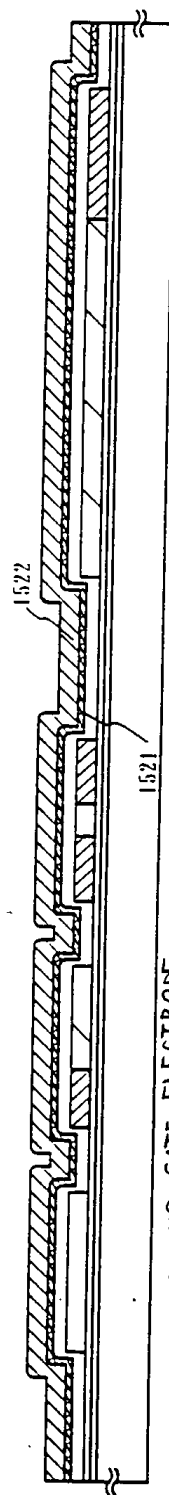
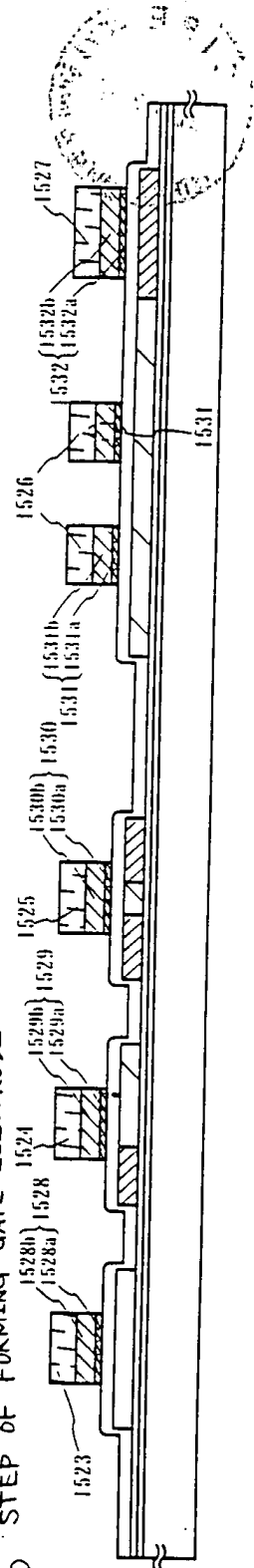


Fig. 15D STEP OF FORMING GATE ELECTRODE



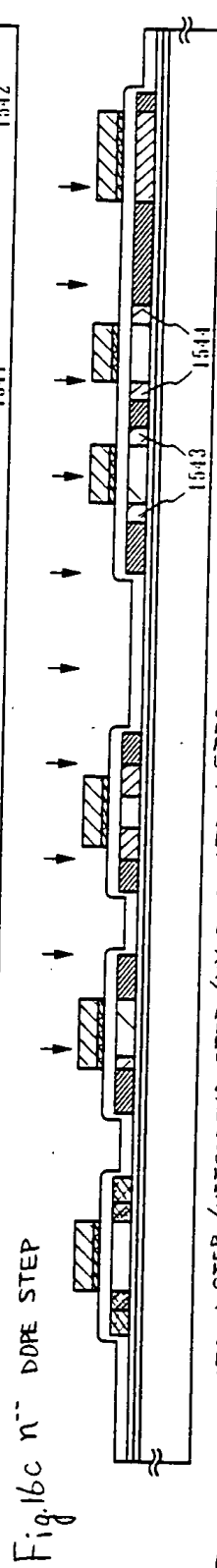
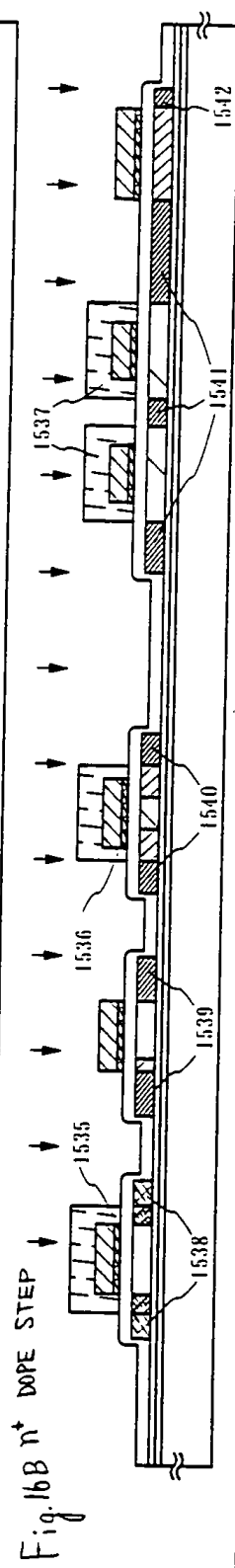
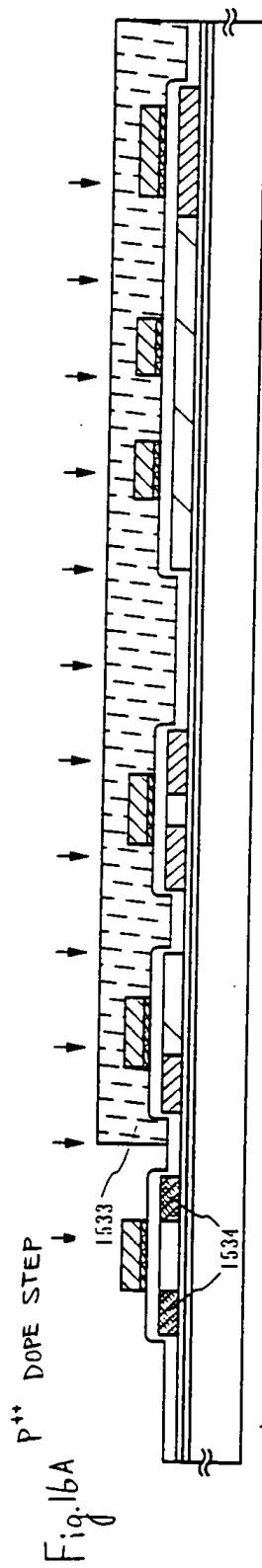
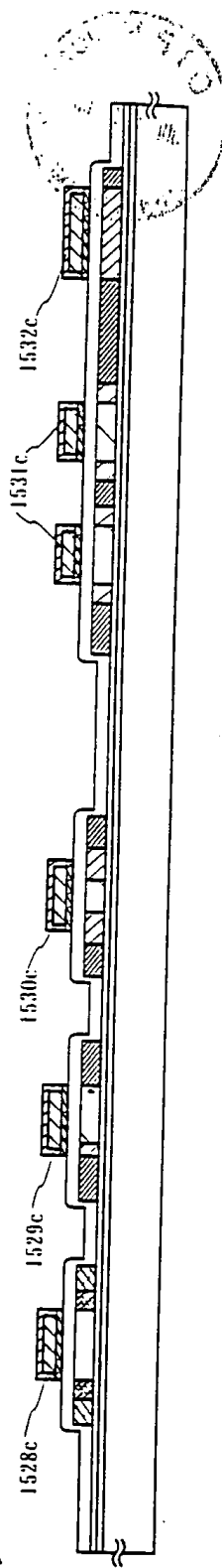
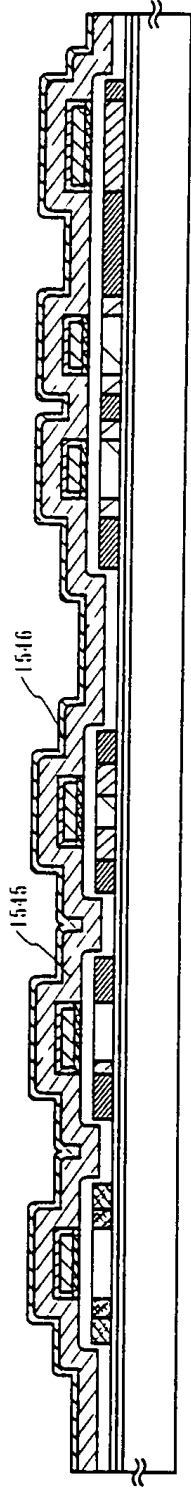


Fig. 16D ACTIVATION STEP/NITRIDING STEP/HYDROGENATION STEP



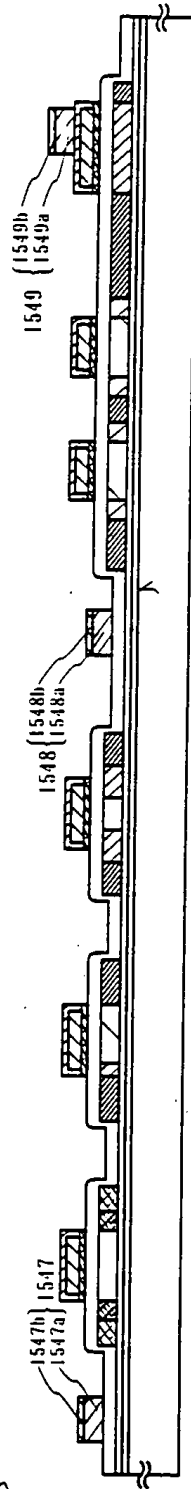
STEP OF FORMING SECOND CONDUCTIVE FILM

Fig. 17A



FORMATION OF GATE WIRING

Fig. 17B



STEP OF FORMING INTERLAYER INSULATING FILM/STEP OF FORMING CONTACT HOLE/STEP OF FORMING WIRING/STEP OF FORMING PASSIVATION FILM

Fig. 17C

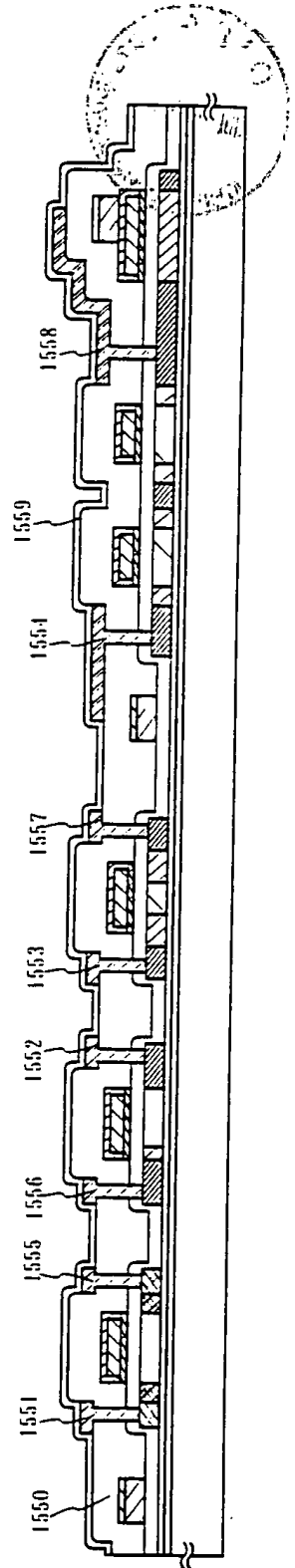
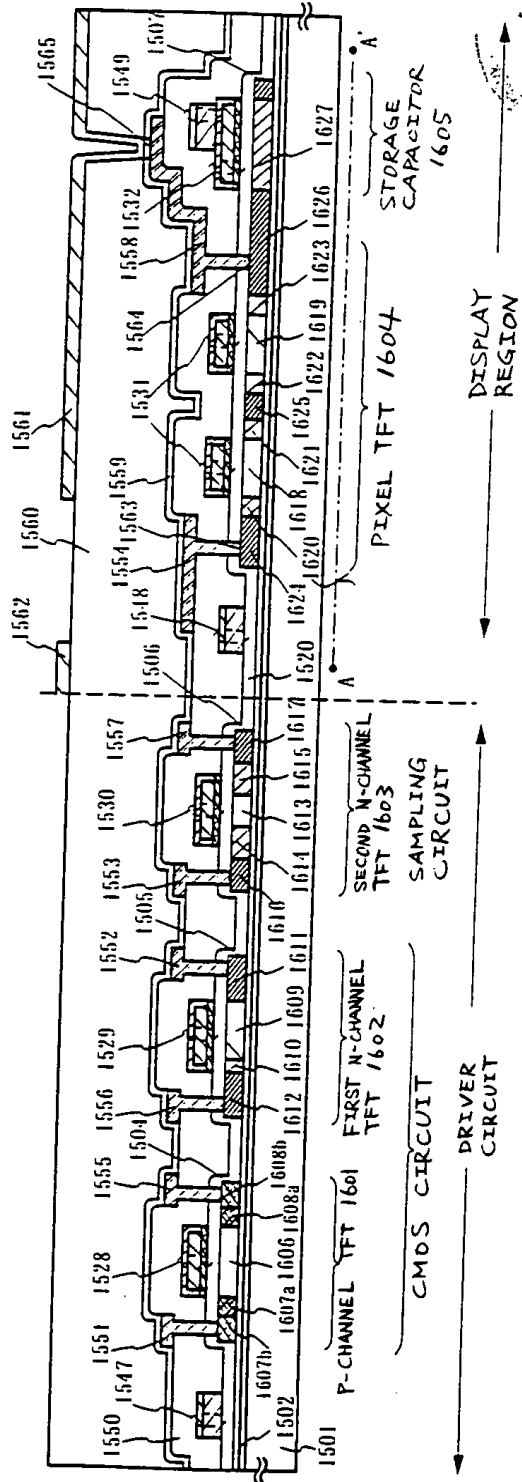


Fig. 18 STEP OF FORMING RESIN FILM/STEP OF FORMING CONTACT HOLE/
STEP OF FORMING PIXEL ELECTRODE



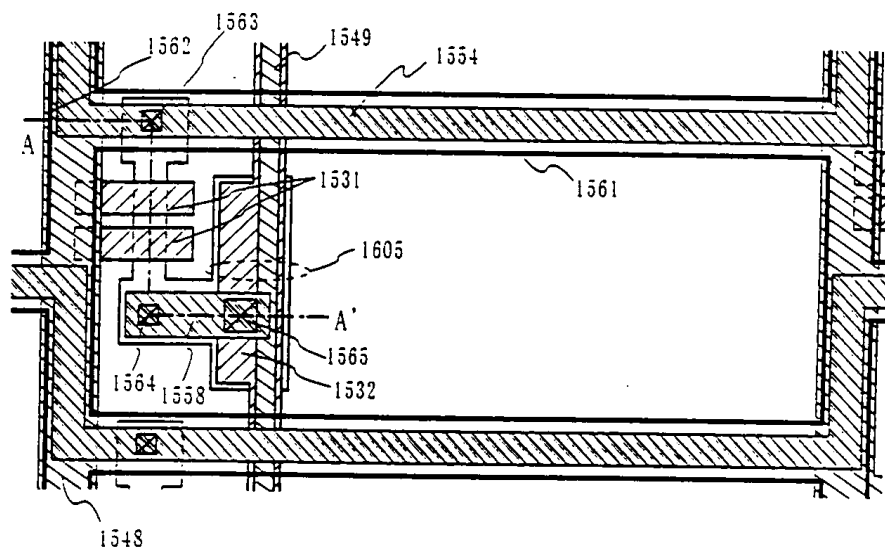


Fig. 19

Fig. 20

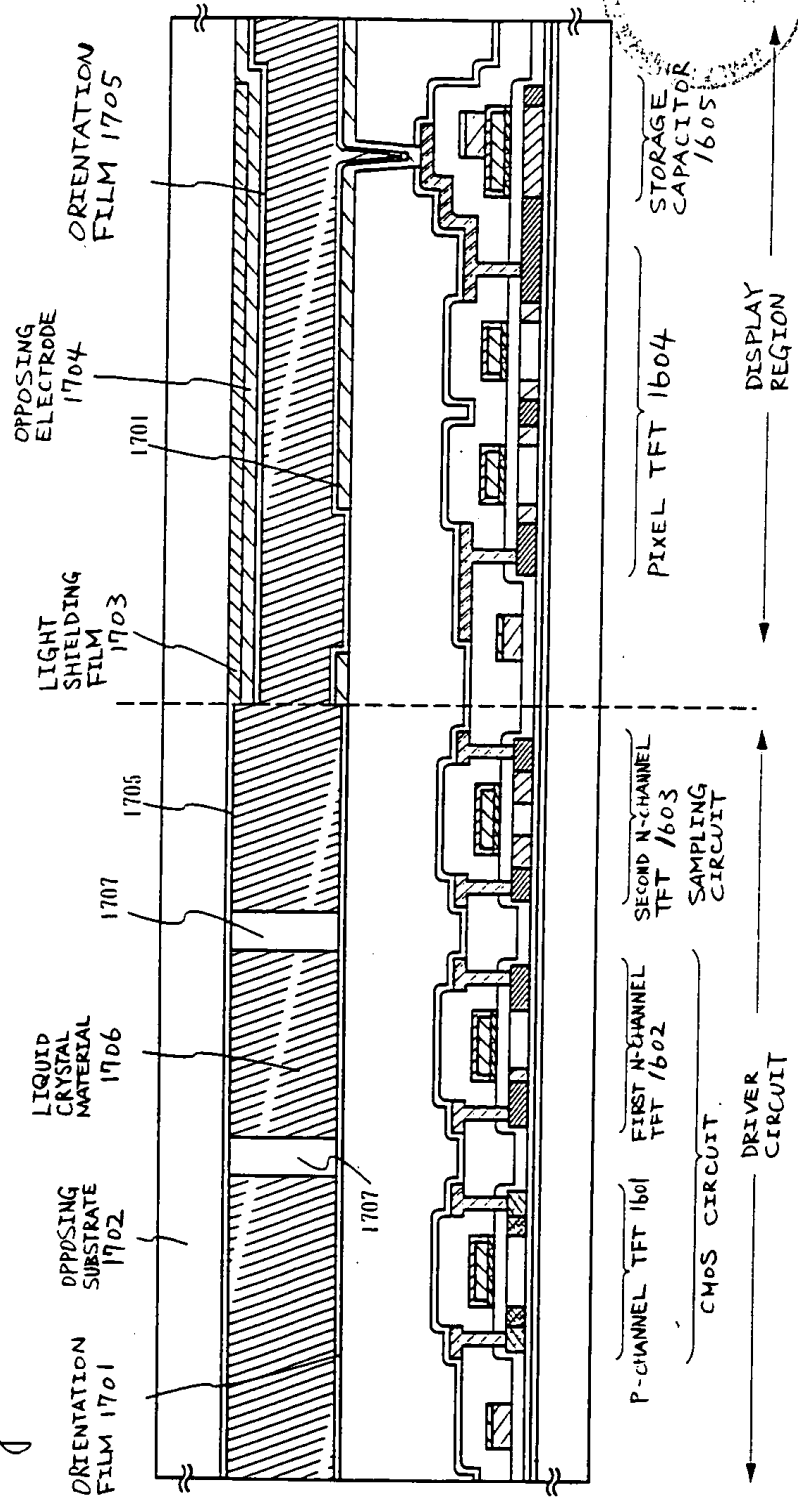


Fig. 21A

STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

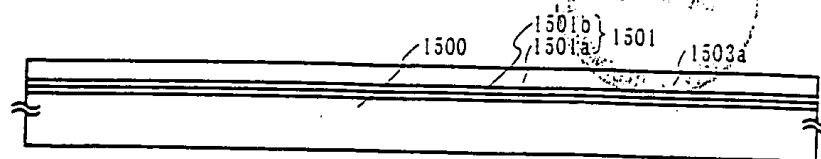


Fig. 21B

STEP OF ADDING CATALYTIC ELEMENT

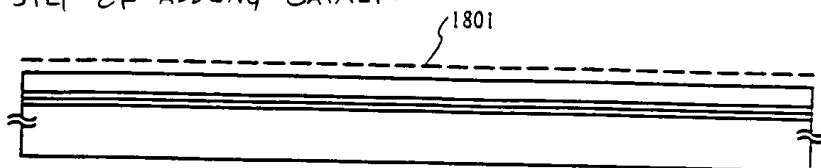


Fig. 21C

LASER ANNEALING STEP

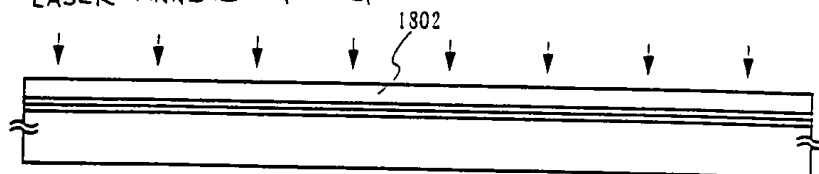


Fig. 22A

STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

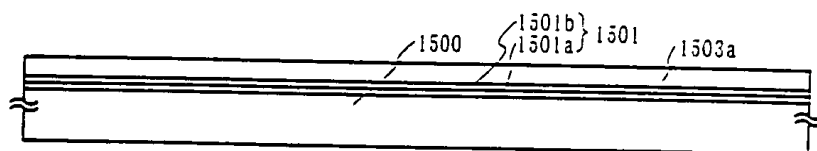


Fig. 22B

STEP OF ADDING CATALYTIC ELEMENT

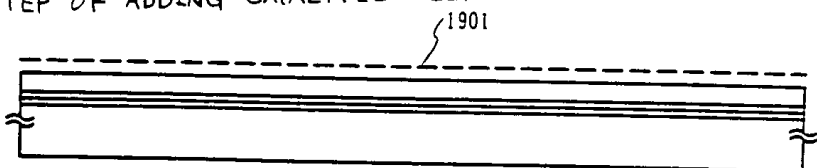


Fig. 22C

CRYSTALLIZATION STEP (HEAT CRYSTALLIZATION)

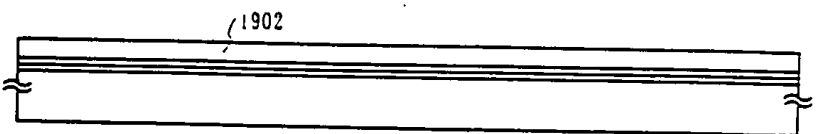


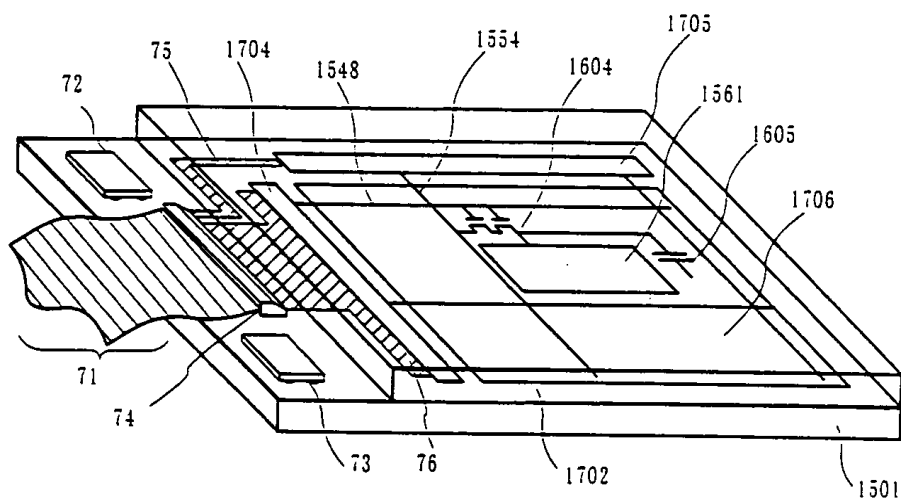
Fig. 22D

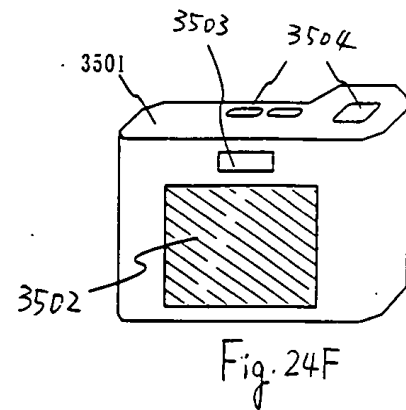
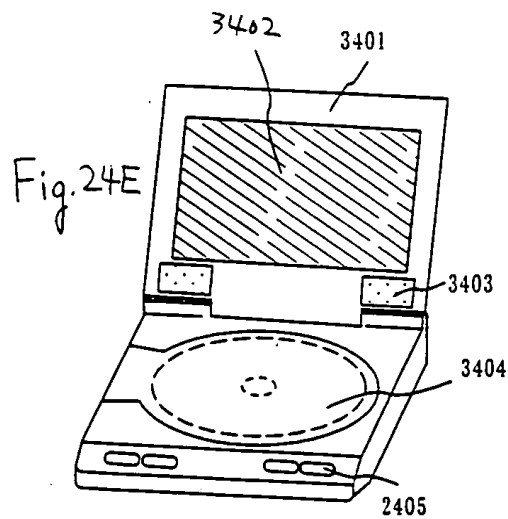
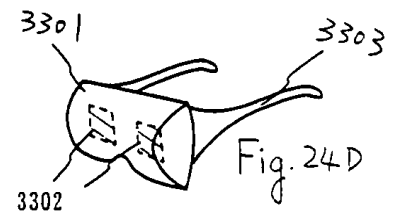
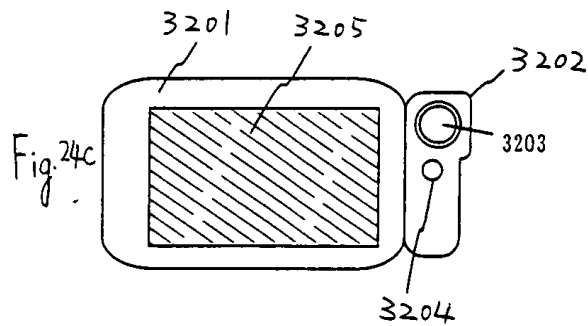
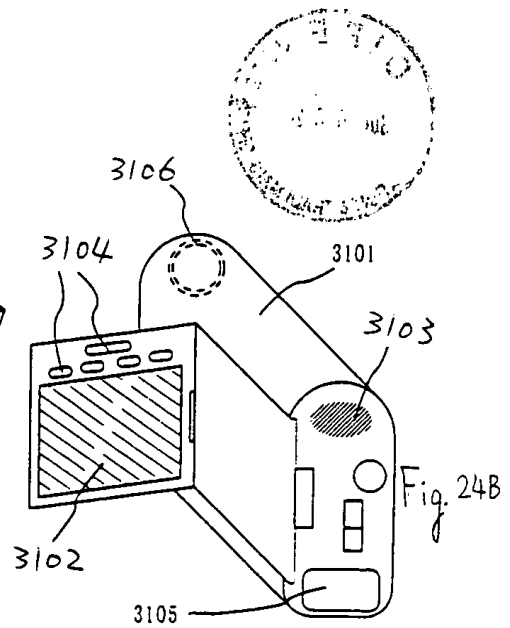
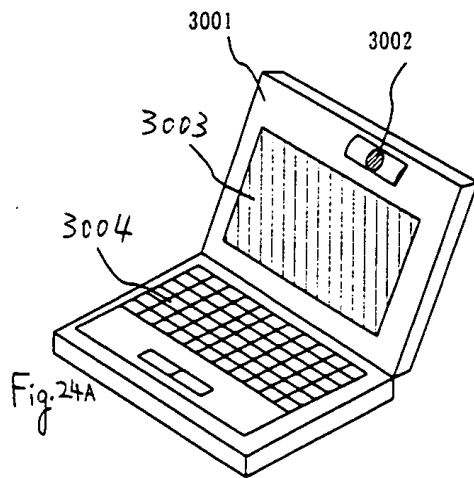
LASER ANNEALING STEP





Fig. 23





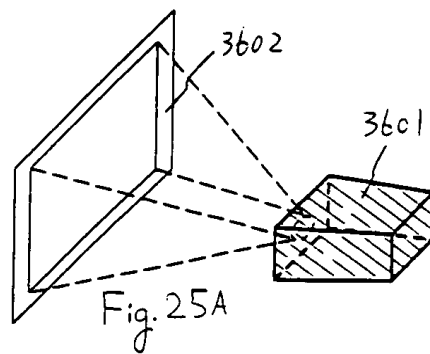


Fig. 25A

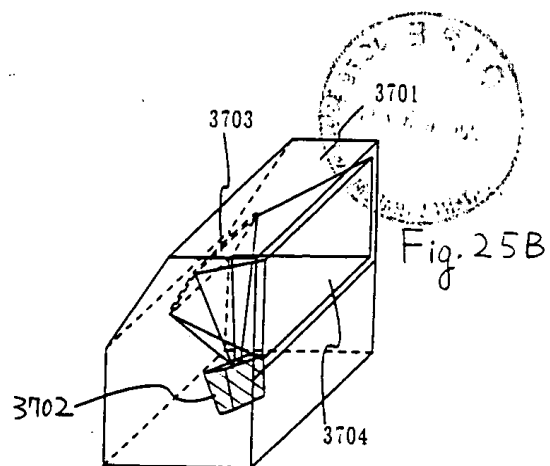


Fig. 25B

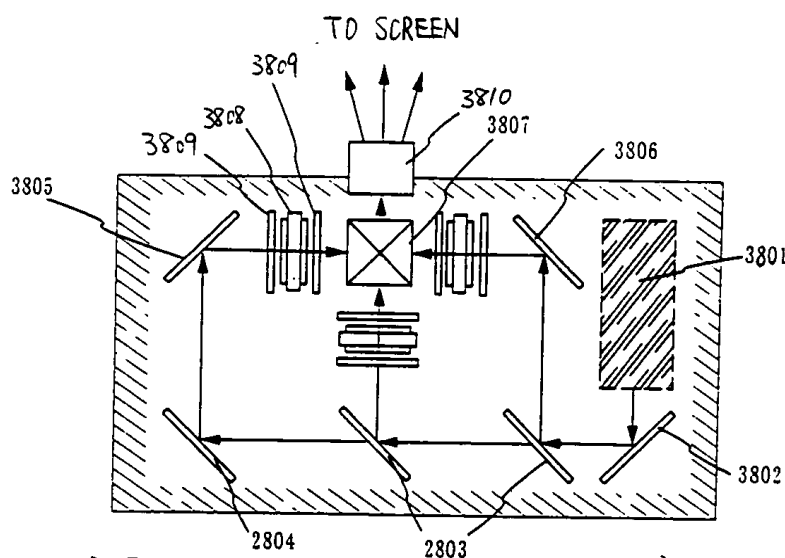


Fig. 25C PROJECTING APPARATUS (THREE-PLATE TYPE)

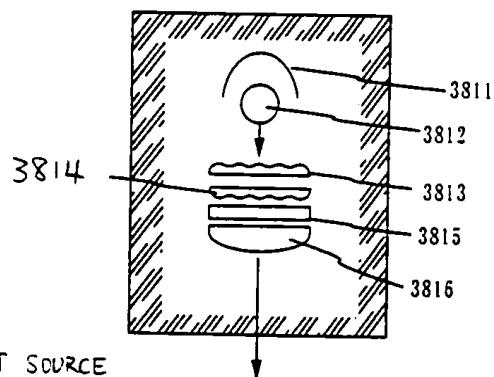


Fig. 25D LIGHT SOURCE OPTICAL SYSTEM

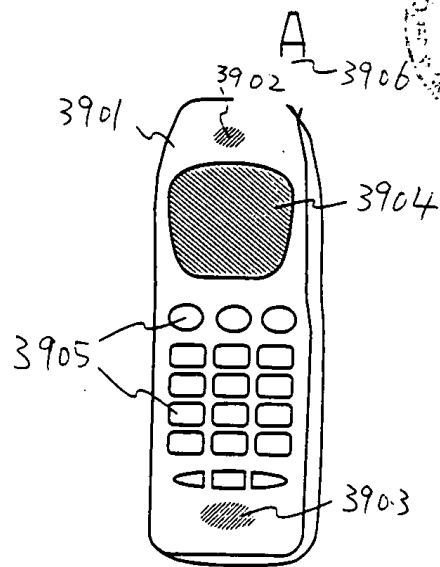


Fig. 26A

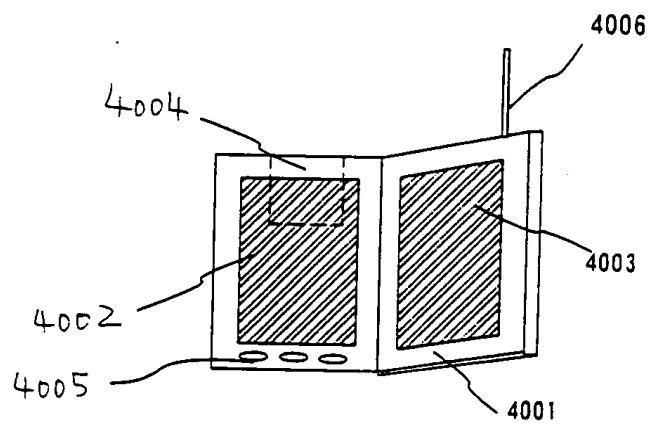


Fig. 26B

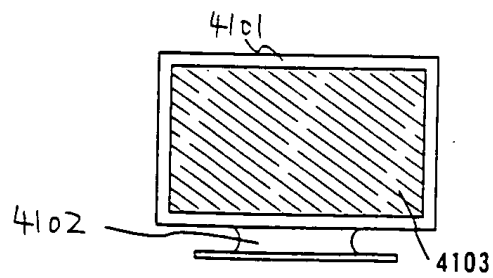


Fig. 26C